

Fig. 1 is a cross-sectional view of a semiconductor device. It shows a substrate 1 with a thin layer 3 on top. Layer 3 has a central region 9 with a different pattern. Above layer 3 is a layer 11. A layer 7 is on top of layer 11, with openings 5 in the central region 9. Dimensions B and A are indicated at the top.

FIG. 1D
BACKGROUND ART

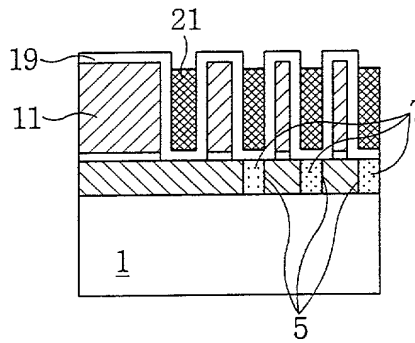


FIG. 1E
BACKGROUND ART

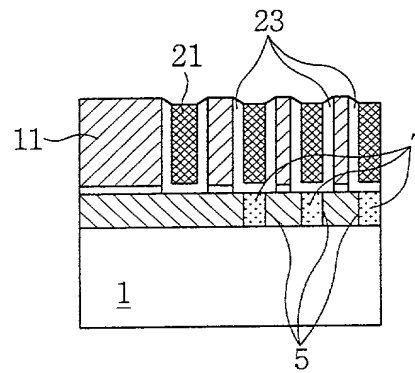


FIG. 1F
BACKGROUND ART

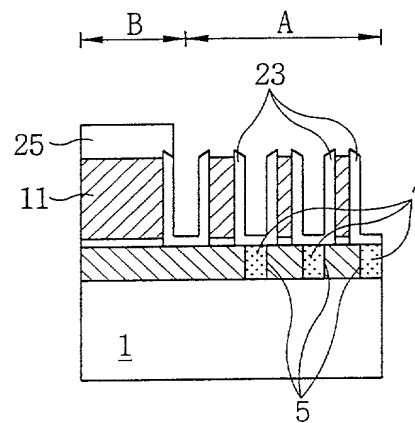


FIG. 1G
BACKGROUND ART

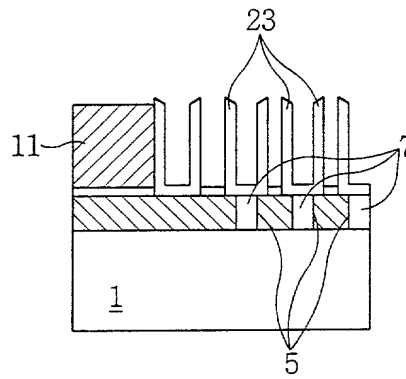


FIG. 2A

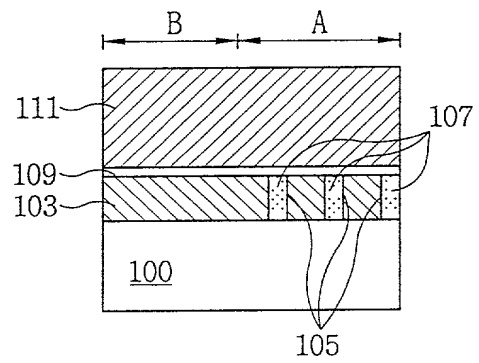
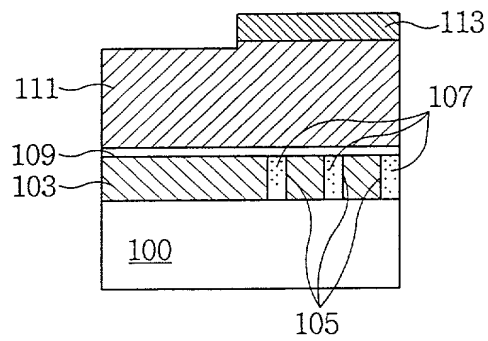


FIG. 2B



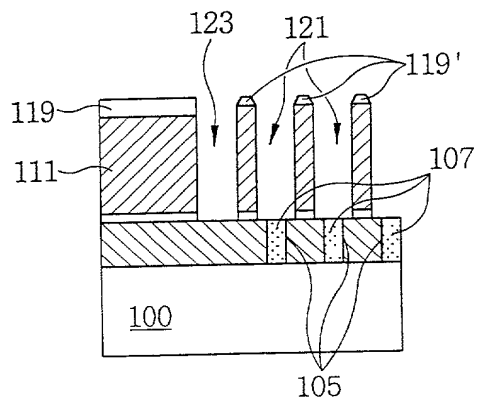
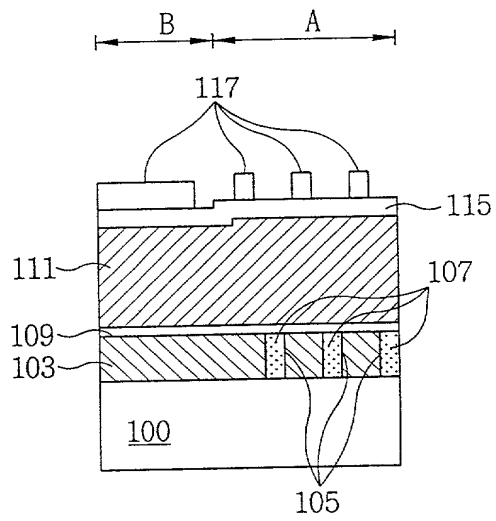
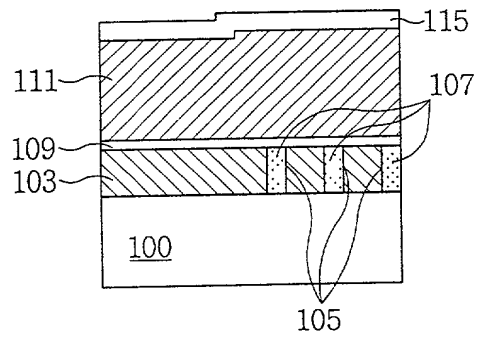


FIG. 2F

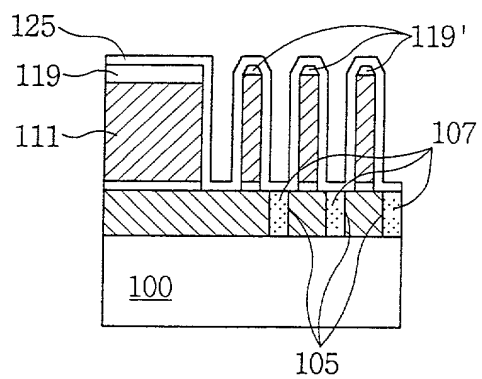


FIG. 2G

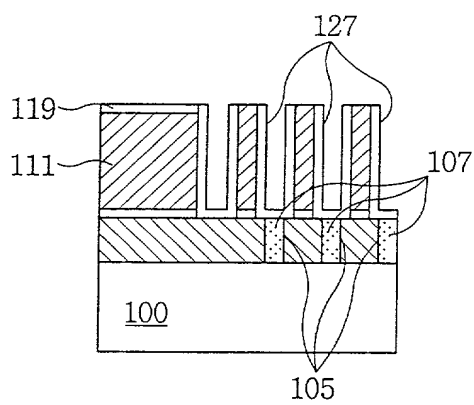


FIG. 2H

